


11/17/03

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	High-Voltage Transistor With A Multi-Layer Conduction Region																								
<div>Application Number: 09/961229</div> <div>Confirmation Number: 4375</div> <div>First Named Applicant: Vladimir Rumennik</div> <div>Attorney Docket Number: 03692.P007XD4</div> <div>Art Unit: 2811</div> <div>Examiner: Shouxiang Hu</div> <div>Search string: (6633065 or 6639277).pn.</div>																									
<div>RECEIVED NOV 28 2003 TECHNICAL CENTER 2800</div> <div></div>																									
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This information disclosure statement is being submitted concurrent with the filing of a Request for Continued Examination in the above-referenced application.																									
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<p>Application Number: 09/981229 Confirmation Number: 4375 First Named Applicant: Vladimir Rumennik Attorney Docket Number: 03692.P007XD4 Art Unit: 2811 Examiner: Shouxiang Hu. Search string: (4614959 or 5294824).pn.</p> <p>US Patent Documents</p> <p>Note: Applicant is not required to submit a paper copy of cited US Patent Documents</p> <table border="1"><thead><tr><th>Init</th><th>Cite.No.</th><th>Patent No.</th><th>Date</th><th>Patentee</th><th>Kind</th><th>Class</th><th>Subclass</th></tr></thead><tbody><tr><td>SK</td><td>1</td><td>4614959</td><td>1986-09-01</td><td>Nakagawa</td><td></td><td></td><td></td></tr><tr><td>SK</td><td>2</td><td>5294824</td><td>1994-03-01</td><td>Okada</td><td></td><td></td><td></td></tr></tbody></table> <p>Signature</p> <table border="1"><thead><tr><th>Examiner Name</th><th>Date</th></tr></thead><tbody><tr><td><i>Shouxiang Hu</i></td><td>6/28/04</td></tr></tbody></table>		Init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass	SK	1	4614959	1986-09-01	Nakagawa				SK	2	5294824	1994-03-01	Okada				Examiner Name	Date	<i>Shouxiang Hu</i>	6/28/04
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